

In re: Sumakeris et al.
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Page 3

APPENDIX: MARKED AMENDMENTS

[0001] This invention was developed with Government support under Government contracts F33615-01-2-2108 and F33615-00-C-5403. The Government may have certain rights in this invention. The present invention relates to increasing the quality and desired properties of semiconductor materials used in electronic devices, particularly power electronic devices. In particular, the invention relates to an improved process for minimizing crystal defects in silicon carbide, and the resulting improved structures and devices.

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